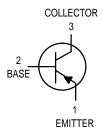
Switching Transistor PNP Silicon



MAXIMUM RATINGS

III/Juliioiii TATIITOO					
Rating	Symbol	Value	Unit		
Collector-Emitter Voltage	VCEO	-25	Vdc		
Collector-Emitter Voltage	VCES	-25	Vdc		
Collector-Base Voltage	VCBO	-25	Vdc		
Emitter-Base Voltage	VEBO	-4.0	Vdc		
Collector Current — Continuous	IC	-500	mAdc		
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C		
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C		

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}^{(1)}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•			
Collector–Emitter Breakdown Voltage (I _C = –100 μAdc, V _{BE} = 0)	V(BR)CES	-25	_	Vdc
Collector-Emitter Sustaining Voltage ⁽²⁾ $(I_C = -10 \text{ mAdc}, I_B = 0)$	VCEO(sus)	-25	_	Vdc
Collector-Base Breakdown Voltage (I _C = -100 μAdc, I _E = 0)	V(BR)CBO	-25	_	Vdc
Emitter-Base Breakdown Voltage (IE = -100 μAdc, IC = 0)	V(BR)EBO	-4.0	_	Vdc
Collector Cutoff Current (VCE = -15 Vdc, VBE = 0) (VCE = -15 Vdc, VBE = 0, TA = -65° C)	ICES	_ _	-0.035 -2.0	μAdc
Emitter Cutoff Current $(V_{EB} = -3.0 \text{ V}, I_{C} = 0)$	I _{EBO}	_	-35	nA
Base Current $(V_{CE} = -15 \text{ Vdc}, V_{BE} = 0)$	IB	_	-0.035	μAdc

- 1. $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.
- 2. Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2.0%.

(Replaces MPS3638/D)



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ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted) (Continued)

	Symbol	Min	Max	Unit	
ON CHARACTER	RISTICS(2)	•			
DC Current Gain $(I_C = -1.0 \text{ mAdc},$ $(I_C = -10 \text{ mAdc},$ $(I_C = -50 \text{ mAdc},$ $(I_C = -300 \text{ mAdc})$	hFE	80 100 100 20	_ _ _ _	_	
Collector – Emitter S (IC = -50 mAdc, (IC = -300 mAdc)	VCE(sat)	_	-0.25 -1.0	Vdc	
Base – Emitter Satu (IC = –50 mAdc, (IC = –300 mAdd	VBE(sat)	 _0.80	-1.1 -2.0	Vdc	
SMALL-SIGNAL	CHARACTERISTICS				
Current-Gain — B (VCE = -3.0 Vdc	andwidth Product $f_{c} = -50 \text{ mAdc}, f = 100 \text{ MHz}$	f _T	150	_	MHz
Output Capacitance (V _{CB} = -10 Vdc,	C _{obo}	_	10	pF	
Input Capacitance (V _{EB} = -0.5 Vdc	C _{ibo}	_	25	pF	
Input Impedance (I _C = -10 mAdc,	Input Impedance (I _C = -10 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)			2000	kΩ
Voltage Feedback (IC = -10 mAdc,	h _{re}	_	15	X 10 ⁻⁴	
Small–Signal Curre (I _C = –10 mAdc,	h _{fe}	100	_	_	
Output Admittance (I _C = -10 mAdc,	h _{oe}	_	1.2	mmhos	
SWITCHING CHA	ARACTERISTICS				
Delay Time	(V _{CC} = -10 Vdc, I _C = -300 mAdc, I _{B1} = -30 mAdc)	t _d	_	20	ns
Rise Time	(*CC = 10 vac, 1C = 300 III/ac, 1B1 = -30 III/ac)	t _r	_	70	ns
Storage Time	$(V_{CC} = -10 \text{ Vdc}, I_{C} = -300 \text{ mAdc},$	t _S	_	140	ns
Fall Time	$I_{B1} = -30 \text{ mAdc}, I_{B2} = -30 \text{ mAdc})$	t _f	_	70	ns
Turn-On Time	urn–On Time (I _C = -300 mAdc , I _{B1} = -30 mAdc)		_	75	ns
Turn–Off Time $(I_C = -300 \text{ mAdc}, I_{B1} = -30 \text{ mAdc}, I_{B2} = 30 \text{ mAdc})$		t _{off}		170	ns

^{2.} Pulse Test: Pulse Width \leq 300 $\mu s;$ Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUIT

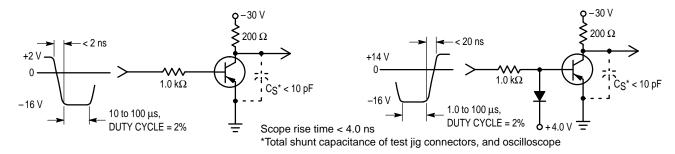
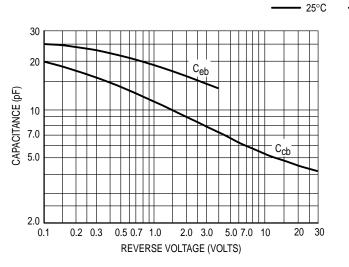


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

TRANSIENT CHARACTERISTICS





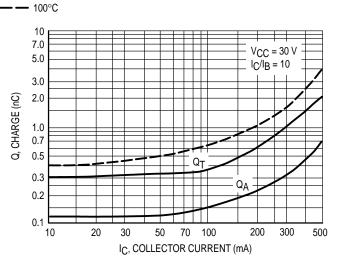
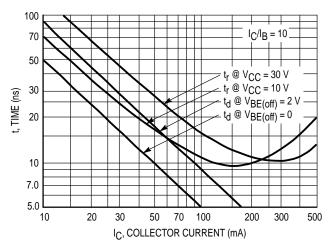


Figure 4. Charge Data

TRANSIENT CHARACTERISTICS (Continued)

—— 25°C —— 100°C



100 70 $V_{CC} = 30 \text{ V}$ $I_{C}/I_{B} = 10$ 50 t_r, RISE TIME (ns) 30 20 10 7.0 5.0 10 20 50 70 100 300 500 IC, COLLECTOR CURRENT (mA)

Figure 5. Turn-On Time

Figure 6. Rise Time

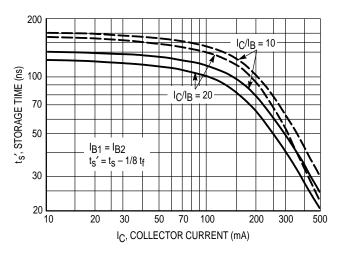


Figure 7. Storage Time

SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $V_{CE} = -10 \text{ Vdc}, T_A = 25^{\circ}\text{C}$ Bandwidth = 1.0 Hz

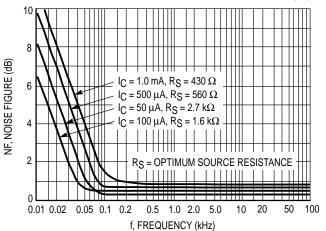


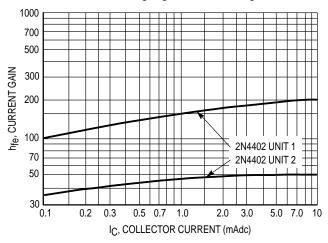
Figure 8. Frequency Effects

Figure 9. Source Resistance Effects

h PARAMETERS

 $V_{CE} = -10 \text{ Vdc}, f = 1.0 \text{ kHz}, T_A = 25^{\circ}\text{C}$

This group of graphs illustrates the relationship between hfe and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were



selected from the 2N4402 line, and the same units were used to develop the correspondingly–numbered curves on each graph.

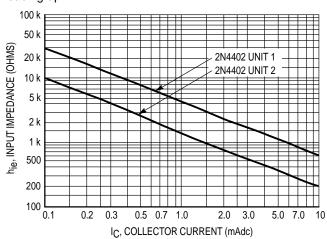


Figure 10. Current Gain

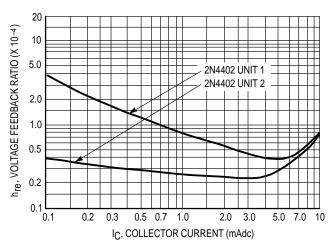


Figure 12. Voltage Feedback Ratio

Figure 11. Input Impedance

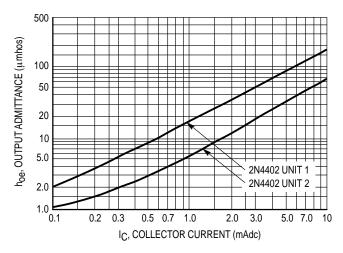


Figure 13. Output Admittance

STATIC CHARACTERISTICS

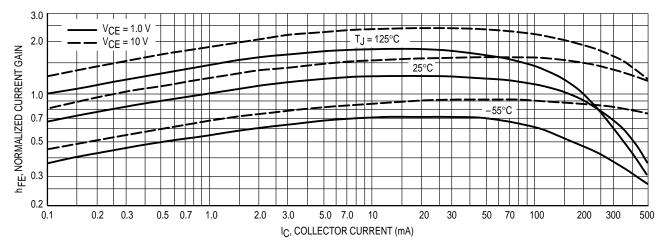


Figure 14. DC Current Gain

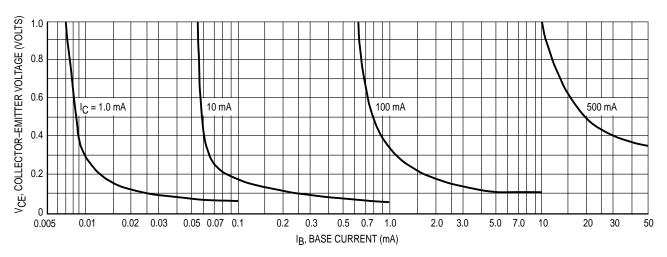


Figure 15. Collector Saturation Region

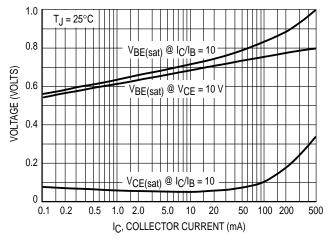


Figure 16. "On" Voltages

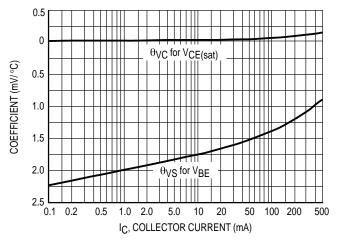
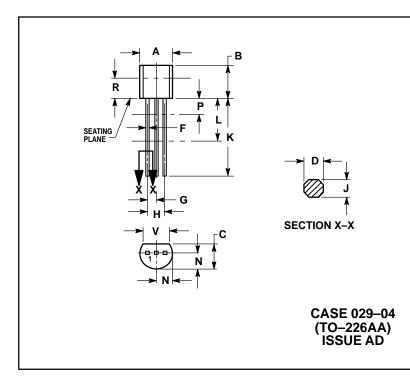


Figure 17. Temperature Coefficients

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J. APPLY BETWEEN L AND K. MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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